

## General Description

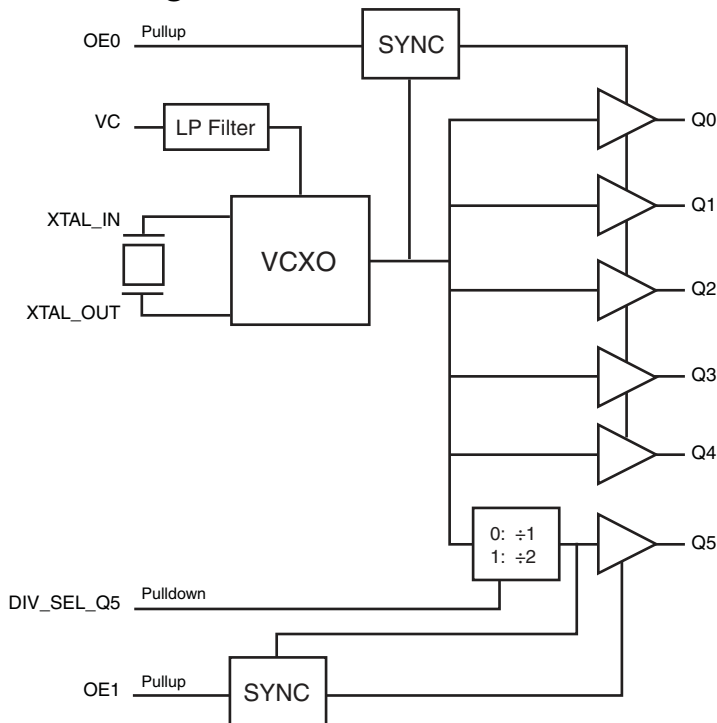
The ICS81006I is a high performance, low jitter/ low phase noise VCXO. The ICS81006I works in conjunction with a pullable crystal to generate an output clock over the range of 12MHz – 31.25MHz and has 6 LVCMOS outputs, effectively integrating a fanout buffer function.

The frequency of the VCXO is adjusted by the VC control voltage input. The output range is  $\pm 100$ ppm around the nominal crystal frequency. The VC control voltage range is 0 –  $V_{DD}$ . The device is packaged in a small 4mm x 4mm VFQFN package and is ideal for use on space constrained boards typically encountered in ADSL/VDSL applications.

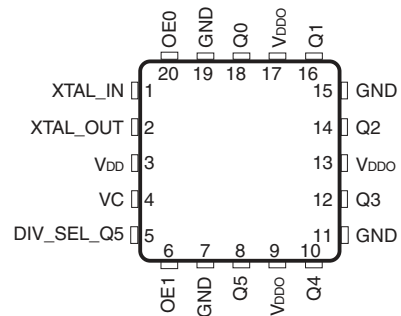
## Features

- Six LVCMOS/LVTTL outputs, 20 $\Omega$  nominal output impedance
- Output Q5 can be selected for  $\div 1$  or  $\div 2$  frequency relative to the crystal frequency
- Output frequency range: 12MHz to 31.25MHz
- Crystal pull range:  $\pm 90$ ppm (typical)
- Synchronous output enable places outputs in High-Impedance state
- On-chip filter on VIN to suppress noise modulation of VCXO
- $V_{DD}/V_{DDO}$  combinations
  - 3.3V/3.3V
  - 3.3V/2.5V
  - 3.3V/1.8V
  - 2.5V/2.5V
  - 2.5V/1.8V
- 4mm x 4mm 20-Lead VFQFN package is ideal for space constrained designs
- -40°C to 85°C ambient operating temperature
- Lead-free (RoHS 6) packaging

## Block Diagram



## Pin Assignment



**ICS81006I**

**20-Lead VFQFN**

**4mm x 4mm x 0.925 package body  
K Package**

**Top View**

## Pin Descriptions and Characteristics

Table 1. Pin Descriptions<sup>1</sup>

Number	Name	Type		Description
1, 2	XTAL_IN, XTAL_OUT	Input		Crystal oscillator interface. XTAL_IN is the input. XTAL_OUT is the output.
3	V <sub>DD</sub>	Power		Positive supply pin.
4	VC	Input		Control voltage input.
5	DIV_SEL_Q5	Input	Pulldown	Output divider select pin for Q5 output. When LOW, ÷1. When HIGH, ÷2. LVCMOS/LVTTL interface levels.
6	OE1	Input	Pullup	Output enable pin. When HIGH, Q5 output is enabled. When LOW, forces Q5 to a high impedance state. LVCMOS/LVTTL interface levels.
7, 11, 15, 19	GND	Power		Power supply ground.
8, 10, 12, 14, 16, 18	Q5, Q4, Q3, Q2, Q1, Q0	Output		Single-ended clock outputs. LVCMOS/LVTTL interface levels. 20Ω output impedance.
9, 13, 17	V <sub>DDO</sub>	Power		Output supply pins.
20	OE0	Input	Pullup	Output enable pin. When HIGH, Q0:Q4 outputs are enabled. When LOW, forces Q0:Q4 to a high impedance state. LVCMOS/LVTTL interface levels.

NOTE 1: *Pullup* and *Pulldown* refers to internal input resistors. See [Table 2, Pin Characteristics](#), for typical values.

Table 2. Pin Characteristics

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
C <sub>IN</sub>	Input Capacitance	OE0, OE1			4		pF
C <sub>PD</sub>	Power Dissipation Capacitance		V <sub>DD</sub> = V <sub>DDO</sub> = 3.465V			3	pF
			V <sub>DD</sub> = 3.465V or 2.625V, V <sub>DDO</sub> = 2.625V			4	pF
			V <sub>DD</sub> = 3.465V or 2.625V, V <sub>DDO</sub> = 2V			6	pF
R <sub>PULLUP</sub>	Input Pullup Resistor				51		kΩ
R <sub>PULLDOWN</sub>	Input Pulldown Resistor				51		kΩ
R <sub>OUT</sub>	Output Impedance		V <sub>DDO</sub> = 3.3V			20	Ω
			V <sub>DDO</sub> = 2.5V			25	Ω
			V <sub>DDO</sub> = 1.8V			38	Ω

## Absolute Maximum Ratings

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Electrical Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Item	Rating
Supply Voltage, $V_{DD}$	4.6V
Inputs, $V_I$	-0.5V to $V_{DD} + 0.5V$
Outputs, $V_O$	-0.5V to $V_{DDO} + 0.5V$
Package Thermal Impedance, $\theta_{JA}$	60.4°C/W (0 mps)
Storage Temperature, $T_{STG}$	-65°C to 150°C

## DC Electrical Characteristics

**Table 3A. Power Supply DC Characteristics,  $V_{DD} = 3.3V \pm 5\%$ ,  $V_{DDO} = 3.3V \pm 5\%$ ,  $2.5V \pm 5\%$  or  $1.8V \pm 0.2V$ ,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$**

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$V_{DD}$	Positive Supply Voltage		3.135	3.3	3.465	V
$V_{DDO}$	Output Supply Voltage		3.135	3.3	3.465	V
			2.375	2.5	2.625	V
			1.6	1.8	2.0	V
$I_{DD}$	Power Supply Current				50	mA
$I_{DDO}$	Output Supply Current				20	mA

**Table 3B. Power Supply DC Characteristics,  $V_{DD} = 2.5V \pm 5\%$ ,  $V_{DDO} = 2.5V \pm 5\%$  or  $1.8V \pm 0.2V$ ,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$**

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$V_{DD}$	Positive Supply Voltage		2.375	2.5	2.625	V
$V_{DDO}$	Output Supply Voltage		2.375	2.5	2.625	V
			1.6	1.8	2.0	V
$I_{DD}$	Power Supply Current				50	mA
$I_{DDO}$	Output Supply Current				20	mA

**Table 3C. LVCMOS/LVTTL DC Characteristics,  $T_A = -40^{\circ}\text{C}$  to  $85^{\circ}\text{C}$** 

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
$V_{IH}$	Input High Voltage		$V_{DD} = 3.3\text{V} \pm 5\%$	2		$V_{DD} + 0.3$	V
			$V_{DD} = 2.5\text{V} \pm 5\%$	1.7		$V_{DD} + 0.3$	V
$V_{IL}$	Input Low Voltage	OE0, OE1, DIV_SEL_Q5	$V_{DD} = 3.3\text{V} \pm 5\%$	-0.3		0.8	V
			$V_{DD} = 2.5\text{V} \pm 5\%$	-0.3		0.7	V
VC	VCXO Control Voltage			0		$V_{DD}$	V
$I_{IH}$	Input High Current	DIV_SEL_Q5	$V_{DD} = 3.3\text{V}$ or $2.5\text{V} \pm 5\%$			150	$\mu\text{A}$
		OE0, OE1	$V_{DD} = 3.3\text{V}$ or $2.5\text{V} \pm 5\%$			5	$\mu\text{A}$
$I_{IL}$	Input Low Current	DIV_SEL_Q5	$V_{DD} = 3.3\text{V}$ or $2.5\text{V} \pm 5\%$	-5			$\mu\text{A}$
		OE0, OE1	$V_{DD} = 3.3\text{V}$ or $2.5\text{V} \pm 5\%$	-150			$\mu\text{A}$
$I_I$	Input Current of VC pin		$V_{DD} = 3.465\text{V}$ or $2.625\text{V}$	-100		100	$\mu\text{A}$
$V_{OH}$	Output High Voltage <sup>1</sup>		$V_{DDO} = 3.3\text{V} \pm 5\%$	2.6			V
			$V_{DDO} = 2.5\text{V} \pm 5\%$	1.8			V
			$V_{DDO} = 1.8\text{V} \pm 0.2\text{V}$	1.5			V
$V_{OL}$	Output Low Voltage <sup>1</sup>		$V_{DDO} = 3.3\text{V}$ or $2.5\text{V} \pm 5\%$			0.5	V
			$V_{DDO} = 1.8\text{V} \pm 0.2\text{V}$			0.4	V

NOTE 1: Outputs terminated with  $50\Omega$  to  $V_{DDO}/2$ . See [Parameter Measurement Information](#) section, "Load Test Circuit" diagrams.

## AC Characteristics

**Table 4A. AC Characteristics,  $V_{DD} = V_{DDO} = 3.3V \pm 5\%$ ,  $T_A = -40^\circ C$  to  $85^\circ C$** 

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$f_{OUT}$	Output Frequency		12	19.44	31.25	MHz
$f_{jit}(\emptyset)$	RMS Phase Jitter (Random) <sup>1</sup>	Integration Range: 1kHz – 1MHz		0.35		ps
tsk(o)	Output Skew <sup>2, 3</sup>	Q0:Q4			30	ps
		Q0:Q5	DIV_SEL_Q5 = ÷1		100	ps
$t_R / t_F$	Output Rise/Fall Time	20% to 80%	200		750	ps
odc	Output Duty Cycle		44		56	%

NOTE 1: Refer to the [Phase Noise Plot](#).

NOTE 2: Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at the output differential crosspoints.

NOTE 3: This parameter is defined in accordance with JEDEC Standard 65.

**Table 4B. AC Characteristics,  $V_{DD} = 3.3V \pm 5\%$ ,  $V_{DDO} = 2.5V \pm 5\%$ ,  $T_A = -40^\circ C$  to  $85^\circ C$** 

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$f_{OUT}$	Output Frequency		12	19.44	31.25	MHz
$f_{jit}(\emptyset)$	RMS Phase Jitter (Random) <sup>1</sup>	Integration Range: 1kHz – 1MHz		0.38		ps
tsk(o)	Output Skew <sup>2, 3</sup>	Q0:Q4			20	ps
		Q0:Q5	DIV_SEL_Q5 = ÷1		90	ps
$t_R / t_F$	Output Rise/Fall Time	20% to 80%	300		800	ps
odc	Output Duty Cycle		45		55	%

NOTE 1: Refer to the [Phase Noise Plot](#).

NOTE 2: Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at the output differential crosspoints.

NOTE 3: This parameter is defined in accordance with JEDEC Standard 65.

**Table 4C. AC Characteristics,  $V_{DD} = 3.3V \pm 5\%$ ,  $V_{DDO} = 1.8V \pm 0.2V$ ,  $T_A = -40^\circ C$  to  $85^\circ C$** 

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$f_{OUT}$	Output Frequency		12	19.44	31.25	MHz
$f_{jit}(\emptyset)$	RMS Phase Jitter (Random) <sup>1</sup>	Integration Range: 1kHz – 1MHz		0.27		ps
tsk(o)	Output Skew <sup>2, 3</sup>	Q0:Q4			50	ps
		Q0:Q5	DIV_SEL_Q5 = ÷1		180	ps
$t_R / t_F$	Output Rise/Fall Time	20% to 80%	450		1400	ps
odc	Output Duty Cycle		45		55	%

NOTE 1: Refer to the [Phase Noise Plot](#).

NOTE 2: Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at the output differential crosspoints.

NOTE 3: This parameter is defined in accordance with JEDEC Standard 65.

**Table 4D. AC Characteristics,  $V_{DD} = V_{DDO} = 2.5V \pm 5\%$ ,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$** 

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$f_{OUT}$	Output Frequency		12	19.44	31.25	MHz
$\overline{jit}(\emptyset)$	RMS Phase Jitter (Random) <sup>1</sup>	Integration Range: 1kHz – 1MHz		0.28		ps
tsk(o)	Output Skew <sup>2, 3</sup>	Q0:Q4			25	ps
		Q0:Q5	DIV_SEL_Q5 = ÷1		105	ps
$t_R / t_F$	Output Rise/Fall Time	20% to 80%	300		800	ps
odc	Output Duty Cycle		45		55	%

NOTE 1: Refer to the [Phase Noise Plot](#).

NOTE 2: Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at the output differential crosspoints.

NOTE 3: This parameter is defined in accordance with JEDEC Standard 65.

**Table 4E. AC Characteristics,  $V_{DD} = 2.5V \pm 5\%$ ,  $V_{DDO} = 1.8V \pm 0.2V$ ,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$** 

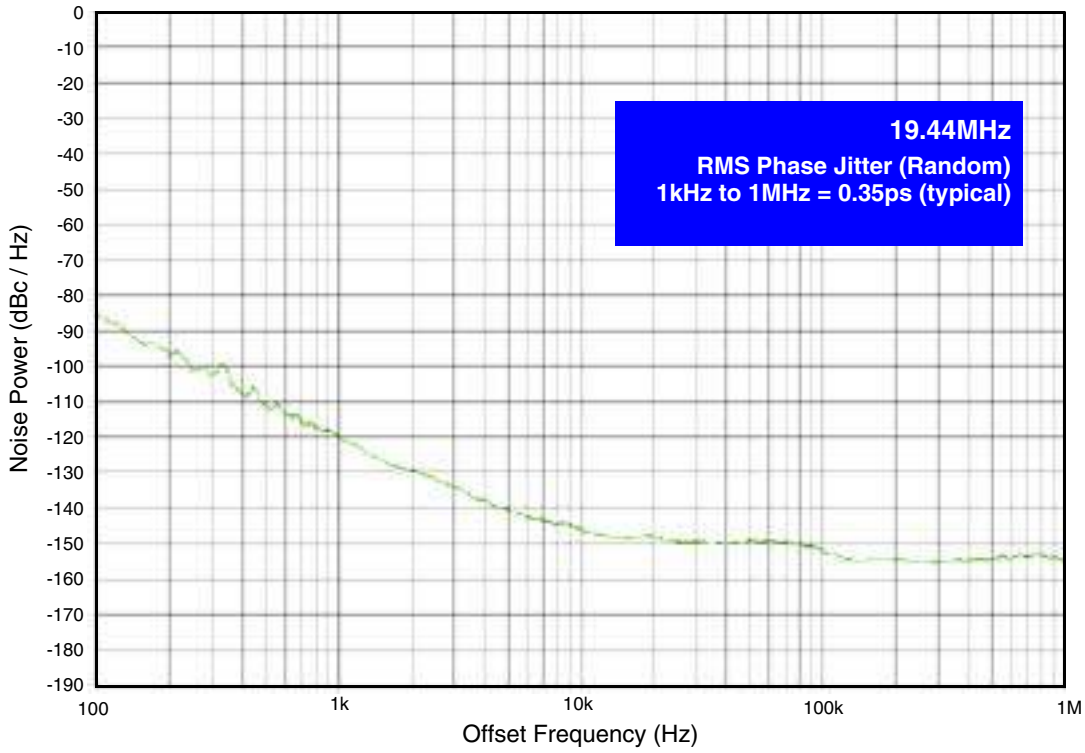
Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$f_{OUT}$	Output Frequency		12	19.44	31.25	MHz
$\overline{jit}(\emptyset)$	RMS Phase Jitter (Random) <sup>1</sup>	Integration Range: 1kHz – 1MHz		0.26		ps
tsk(o)	Output Skew <sup>2, 3</sup>	Q0:Q4			40	ps
		Q0:Q5	DIV_SEL_Q5 = ÷1		185	ps
$t_R / t_F$	Output Rise/Fall Time	20% to 80%	450		1400	ps
odc	Output Duty Cycle		40		60	%

NOTE 1: Refer to the [Phase Noise Plot](#).

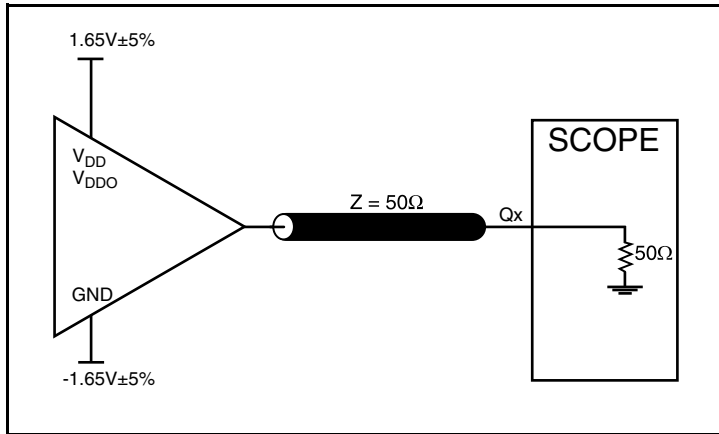
NOTE 2: Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at the output differential crosspoints.

NOTE 3: This parameter is defined in accordance with JEDEC Standard 65.

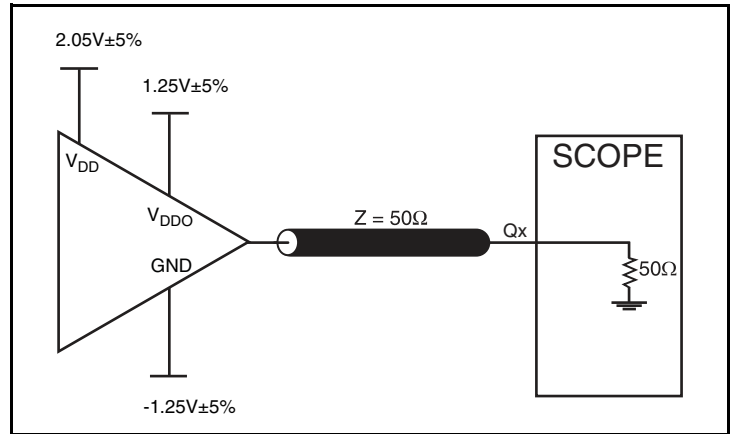
**Typical Phase Noise at 19.44MHz @3.3V CORE/3.3V Output**



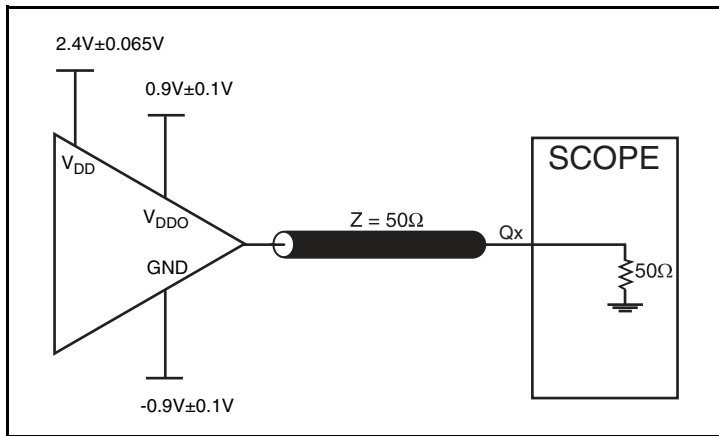
### Parameter Measurement Information



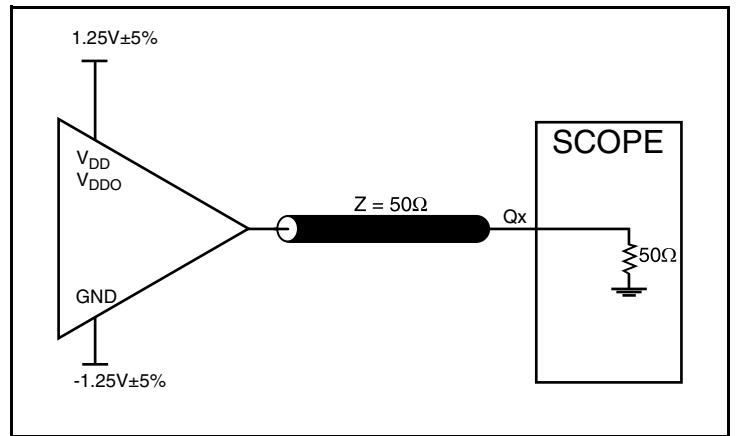
3.3V Core/3.3V Output Load Test Circuit



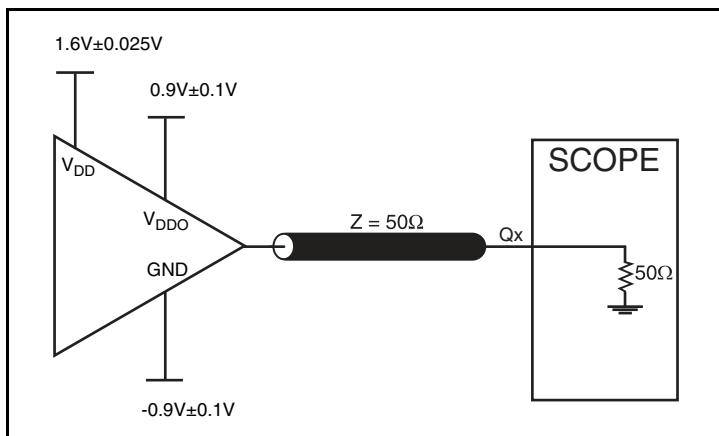
3.3V Core/2.5V Output Load Test Circuit



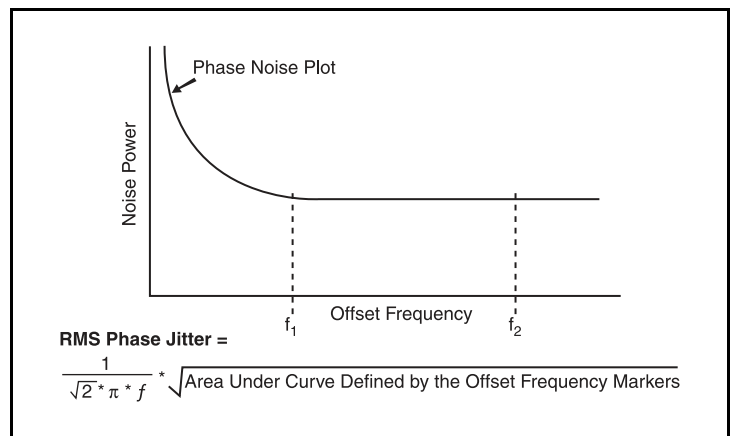
3.3V Core/1.8V Output Load Test Circuit



2.5V Core/2.5V Output Load Test Circuit



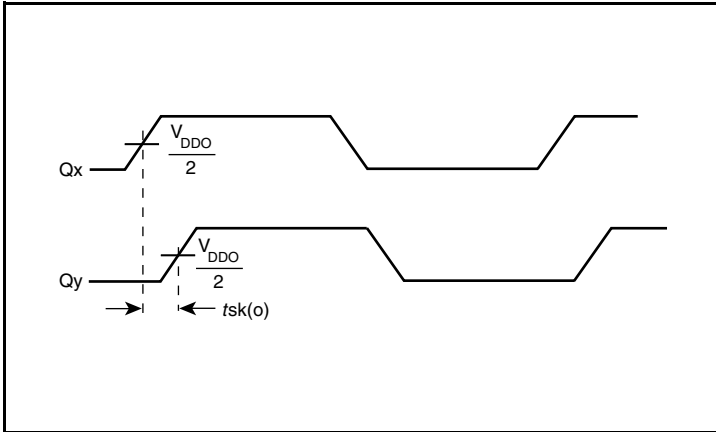
2.5V Core/1.8V Output Load Test Circuit



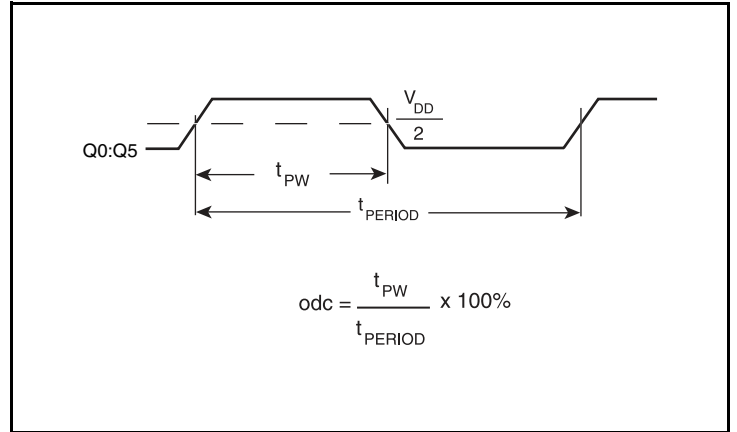
RMS Phase Jitter



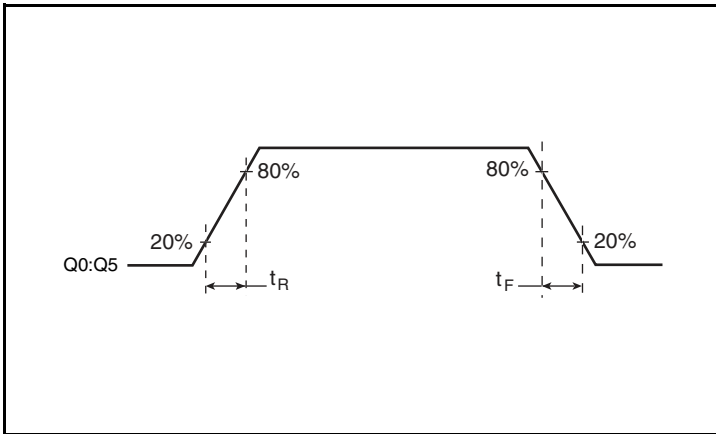
Parameter Measurement Information, Continued



Output Skew



Output Duty Cycle/Pulse Width/Period



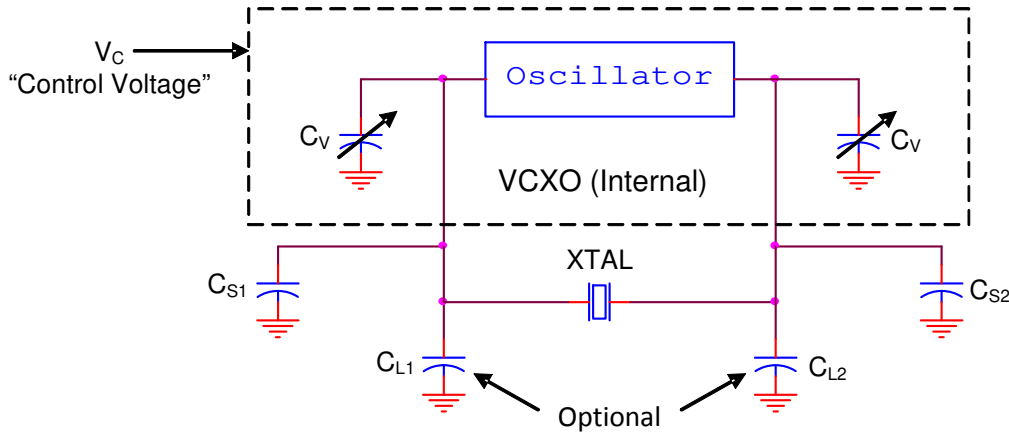
Output Rise/Fall Time

## Applications Information

### VCXO Crystal Selection

Choosing a crystal with the correct characteristics is one of the most critical steps in using a Voltage Controlled Crystal Oscillator (VCXO). The crystal parameters affect the tuning range and accuracy of a

VCXO. Below are the key variables and an example of using the crystal parameters to calculate the tuning range of the VCXO.



**Figure 1. VCXO Oscillator Circuit**

- $V_C$  -Control voltage used to tune frequency
- $C_V$  -Varactor capacitance, varies due to the change in control voltage
- $C_{L1}$   
 $C_{L2}$  -Load tuning capacitance used for fine tuning or centering nominal frequency
- $C_{S1}$   
 $C_{S2}$  -Stray Capacitance caused by pads, vias, and other board parasitics

**Table 5. Example Crystal Parameters**

Symbol	Parameter	Test Conditions	Min	Typical	Max	Units
$f_N$	Nominal Frequency			19.44		MHz
$f_T$	Frequency Tolerance				$\pm 20$	ppm
$f_S$	Frequency Stability				$\pm 20$	ppm
	Operating Temp Range		0		70	$^{\circ}\text{C}$
$C_L$	Load Capacitance			12		pF
$C_O$	Shunt Capacitance			4		pF
$C_O/C_1$	Pullability Ratio			220	240	
ESR	Equivalent Series Resistance				20	
	Drive Level				1	mW
	Aging @ 25 $^{\circ}\text{C}$			$\pm 3$ per year		ppm
	Mode of Operation			Fundamental		

**Table 6. Varactor Parameters**

Symbol	Parameter	Test Condition	Minimum	Typical	Maximum	Unit
$C_{V\_LOW}$	Low Varactor Capacitance	$V_C = 0V$		15.4		pF
$C_{V\_HIGH}$	High Varactor Capacitance	$V_C = 3.3V$		29.6		pF

### Formulas

$$C_{Low} = \frac{(C_{L1} + C_{S1} + C_{V\_Low}) \cdot (C_{L2} + C_{S2} + C_{V\_Low})}{(C_{L1} + C_{S1} + C_{V\_Low}) + (C_{L2} + C_{S2} + C_{V\_Low})}$$

$$C_{High} = \frac{(C_{L1} + C_{S1} + C_{V\_High}) \cdot (C_{L2} + C_{S2} + C_{V\_High})}{(C_{L1} + C_{S1} + C_{V\_High}) + (C_{L2} + C_{S2} + C_{V\_High})}$$

- $C_{Low}$  is the effective capacitance due to the low varactor capacitance, load capacitance and stray capacitance.  $C_{Low}$  determines the high frequency component on the TPR.
- $C_{High}$  is the effective capacitance due to the high varactor capacitance, load capacitance and stray capacitance.  $C_{High}$  determines the low frequency component on the TPR.

$$Total\ Pull\ Range\ (TPR) = \left( \frac{1}{2 \cdot C_0 / C_1 \cdot \left(1 + \frac{C_{Low}}{C_0}\right)} - \frac{1}{2 \cdot C_0 / C_1 \cdot \left(1 + \frac{C_{High}}{C_0}\right)} \right) \cdot 10^6$$

Absolute Pull Range (APR) = Total Pull Range – (Frequency Tolerance + Frequency Stability + Aging)

### Example Calculations

Using the tables and figures above, we can now calculate the TPR and APR of the VCXO using the example crystal parameters. For the numerical example below there were some assumptions made. First, the stray capacitance ( $C_{S1}$ ,  $C_{S2}$ ), which is all the excess capacitance due to board parasitic, is 4pF. Second, the expected lifetime of the project is 5 years; hence the inaccuracy due to aging is  $\pm 15$ ppm.

Third, though many boards will not require load tuning capacitors ( $C_{L1}$ ,  $C_{L2}$ ), it is recommended for long-term consistent performance of the system that two tuning capacitor pads be placed into every design. Typical values for the load tuning capacitors will range from 0 to 4 pF.

$$C_{Low} = \frac{(0 + 4\text{ pf} + 15.4\text{ pf}) \cdot (0 + 4\text{ pf} + 15.4\text{ pf})}{(0 + 4\text{ pf} + 15.4\text{ pf}) + (0 + 4\text{ pf} + 15.4\text{ pf})} = 9.7\text{ pf}$$

$$C_{High} = \frac{(0 + 4\text{ pf} + 29.6\text{ pf}) \cdot (0 + 4\text{ pf} + 29.6\text{ pf})}{(0 + 4\text{ pf} + 29.6\text{ pf}) + (0 + 4\text{ pf} + 29.6\text{ pf})} = 16.8\text{ pf}$$

$$TPR = \left( \frac{1}{2 \cdot 220 \cdot \left(1 + \frac{9.7\text{ pF}}{4\text{ pF}}\right)} - \frac{1}{2 \cdot 220 \cdot \left(1 + \frac{16.8\text{ pF}}{4\text{ pF}}\right)} \right) \cdot 10^6 = 226.5\text{ ppm}$$

TPR =  $\pm 113.25$ ppm

APR =  $113.25$ ppm – (20ppm + 20ppm + 15ppm) =  $\pm 58.25$ ppm

The example above will ensure a total pull range of  $\pm 113.25$  ppm with an APR of  $\pm 58.25$ ppm. Many times, board designers may select their own crystal based on their application. If the application requires a tighter APR, a crystal with better pullability (C0/C1 ratio) can be used.

Also, with the equations above, one can vary the frequency tolerance, temperature stability, and aging or shunt capacitance to achieve the required pullability.

## Recommendations for Unused Input Pins

### Inputs:

#### Control Pins

All control pins have internal pull-ups or pull-downs; additional resistance is not required but can be added for additional protection. A 1kΩ resistor can be used. The VC pin can not be floated.

### Outputs:

#### LVC MOS Outputs

All unused LVC MOS output can be left floating. We recommend that there is no trace attached.

## Schematic Example

Figure 2 shows an example of ICS81006I application schematic. The decoupling capacitors should be located as close as possible to the power pin. For the LVC MOS 20Ω output drivers, series termination

example is shown in the schematic. Additional termination approaches are shown in the LVC MOS Termination Application Note.

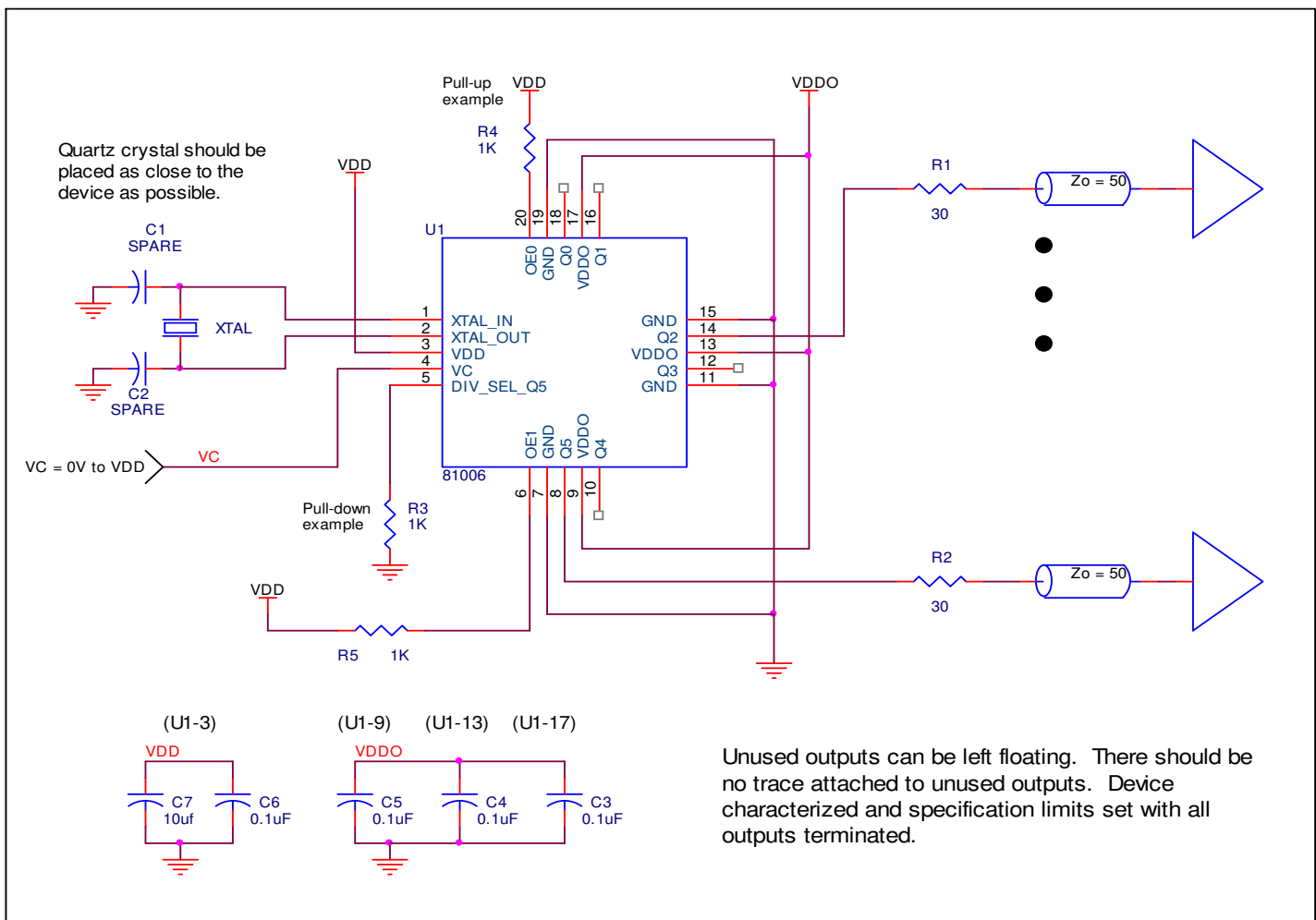


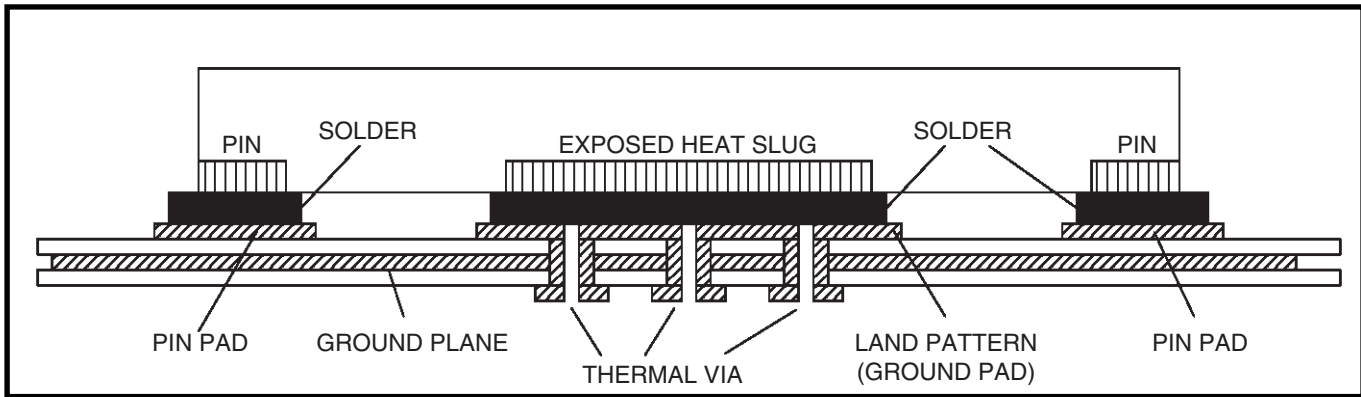
Figure 2. ICS81006I Schematic Example

### VFQFN EPAD Thermal Release Path

In order to maximize both the removal of heat from the package and the electrical performance, a land pattern must be incorporated on the Printed Circuit Board (PCB) within the footprint of the package corresponding to the exposed metal pad or exposed heat slug on the package, as shown in *Figure 3*. The solderable area on the PCB, as defined by the solder mask, should be at least the same size/shape as the exposed pad/slug area on the package to maximize the thermal/electrical performance. Sufficient clearance should be designed on the PCB between the outer edges of the land pattern and the inner edges of pad pattern for the leads to avoid any shorts.

While the land pattern on the PCB provides a means of heat transfer and electrical grounding from the package to the board through a solder joint, thermal vias are necessary to effectively conduct from the surface of the PCB to the ground plane(s). The land pattern must be connected to ground through these vias. The vias act as “heat pipes”. The number of vias (i.e. “heat pipes”) are application specific

and dependent upon the package power dissipation as well as electrical conductivity requirements. Thus, thermal and electrical analysis and/or testing are recommended to determine the minimum number needed. Maximum thermal and electrical performance is achieved when an array of vias is incorporated in the land pattern. It is recommended to use as many vias connected to ground as possible. It is also recommended that the via diameter should be 12 to 13mils (0.30 to 0.33mm) with 1oz copper via barrel plating. This is desirable to avoid any solder wicking inside the via during the soldering process which may result in voids in solder between the exposed pad/slug and the thermal land. Precautions should be taken to eliminate any solder voids between the exposed heat slug and the land pattern. Note: These recommendations are to be used as a guideline only. For further information, please refer to the Application Note on the Surface Mount Assembly of Amkor’s Thermally/Electrically Enhance Leadframe Base Package, Amkor Technology.



**Figure 3. P.C. Assembly for Exposed Pad Thermal Release Path – Side View (drawing not to scale)**

## Reliability Information

**Table 7.  $\theta_{JA}$  vs. Air Flow Table for a 20-Lead VFQFN**

$\theta_{JA}$ vs. Air Flow			
Meters per Second	0	1	3
Multi-Layer PCB, JEDEC Standard Test Boards	60.4°C/W	52.8°C/W	46.0°C/W

## Transistor Count

The transistor count for the ICS81006I is: 983

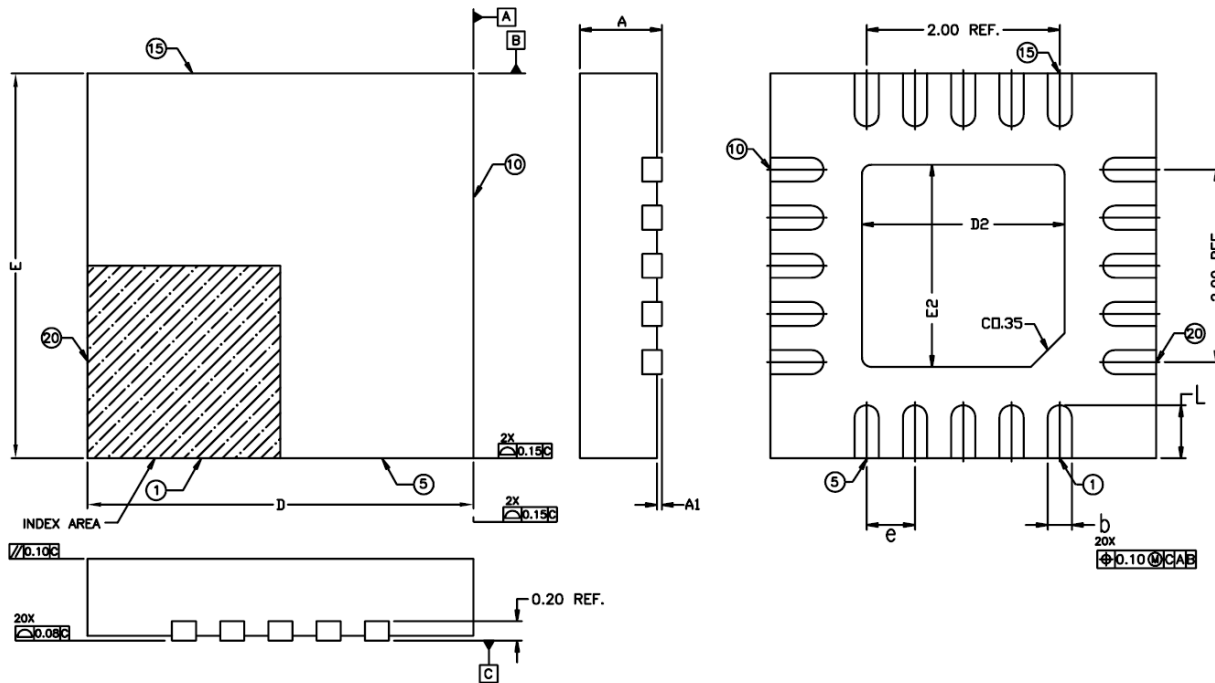
## Package Outline and Package Dimensions

### Package Outline - K Suffix for 20-Lead VFQFN

TOP VIEW

SIDE VIEW

BOTTOM VIEW


**Table 8. Package Dimensions for 20-Lead VFQFN**

All Dimensions in Millimeters			
Symbol	Minimum	Nom	Maximum
b	0.20	0.25	0.30
D	3.90	4.00	4.10
E	3.90	4.00	4.10
D2	1.95	2.10	2.25
E2	1.95	2.10	2.25
L	0.45	0.55	0.65
e	0.50 BSC		
N	20		
A	0.80	0.90	1.00
A1	0.00	0.02	0.05
A3	0.2 REF		

Reference Document: JEDEC Publication 95, MO-220

**NOTE:**

The drawing and dimension data originate from IDT package outline drawing PSC-4170, rev03.

1. Dimensions and tolerances conform to ASME Y14.5M-1994
2. All dimensions are in millimeters. All angles are in degrees.
3. N is the total number of terminals.
4. All specifications comply with JEDEC MO-220.

## Ordering Information

Table 9. Ordering Information

Part/Order Number	Marking	Package	Shipping Packaging	Temperature
81006AKILF	006AIL	"Lead-Free" 20-Lead VFQFN	Tube	-40°C to 85°C
81006AKILFT	006AIL	"Lead-Free" 20-Lead VFQFN	Tape & Reel	-40°C to 85°C



## Revision History Sheet

Rev	Table	Page	Description of Change	Date
B	T4A - T4D  T9	1	General Description and Features section changed output frequency max. from 40MHz to 31.25MHz.	10/8/08
		4-5	AC Tables - changed output frequency from 40MHz max. to 31.25MHz max.	
		6	Added Phase Noise Plot.	
		15	Ordering Information Table - added lead-free marking	
B	T8 T9	15	Updated datasheet to current format.	7/25/14
		15	Updated Package Outline	
		1, 16	Updated package dimensions to reflect tighter tolerances. Removed leaded ordering option.	
B		1	PDN CQ-15-01	2/10/15
B			Added OBSOLETE to the front page.	7/29/16



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